

## CHANGE NOTIFICATION



Linear Technology Corporation  
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(408) 432-1900

April 01, 2014

Dear Sir/Madam:

PCN# 040114

**Subject: Notification of Change to LTC2480 Datasheet**

Please be advised that Linear Technology Corporation has made a change to the LTC2480 specification in order to improve device manufacturability. The Maximum External Oscillator Frequency ( $f_{EOSC}$ ) in the Timing Characteristics is being reduced from 4000kHz to 1000kHz. This is also noted in the text and in the graphs of performance vs. sample rate in Figures 20 to 27 of the attached datasheet. Performance degrades at high sample rates as shown in the figures, and an external oscillator frequency of 1000kHz is a more conservative maximum. No changes are being made to the circuit or the test methodology. Product shipped after June 2, 2014 will be tested to the new limit.

Should you have any further questions, please feel free to contact me at 408-432-1900 ext. 2077, or by email at [JASON.HU@LINEAR.COM](mailto:JASON.HU@LINEAR.COM). If I do not hear from you by June 2, 2014, we will consider this change to be approved by your company.

Sincerely,

Jason Hu  
Quality Assurance Engineer

## ANALOG INPUTS AND DIGITAL OUTPUTS

The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at  $T_A = 25^\circ\text{C}$ . (Note 3)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
$I_{IN}$	Digital Input Current SCK	$0V \leq V_{IN} \leq V_{CC}$ (Note 10)	●	-10	10	$\mu\text{A}$
$C_{IN}$	Digital Input Capacitance $\overline{CS}$ , $f_O$ , SDI			10		pF
$C_{IN}$	Digital Input Capacitance SCK			10		pF
$V_{OH}$	High Level Output Voltage SDO	$I_O = -800\mu\text{A}$	●	$V_{CC} - 0.5$		V
$V_{OL}$	Low Level Output Voltage SDO	$I_O = 1.6\text{mA}$	●		0.4	V
$V_{OH}$	High Level Output Voltage SCK	$I_O = -800\mu\text{A}$	●	$V_{CC} - 0.5$		V
$V_{OL}$	Low Level Output Voltage SCK	$I_O = 1.6\text{mA}$	●		0.4	V
$I_{OZ}$	Hi-Z Output Leakage SDO		●	-10	10	$\mu\text{A}$

## POWER REQUIREMENTS

The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at  $T_A = 25^\circ\text{C}$ . (Note 3)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
$V_{CC}$	Supply Voltage		●	2.7	5.5	V
$I_{CC}$	Supply Current	Conversion Mode (Note 12)	●	160	250	$\mu\text{A}$
		Sleep Mode (Note 12)	●	1	2	$\mu\text{A}$
		H-Grade	●		20	$\mu\text{A}$

## TIMING CHARACTERISTICS

The ● denotes the specifications which apply over the full operating temperature range, otherwise specifications are at  $T_A = 25^\circ\text{C}$ . (Note 3)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
$f_{EOSC}$	External Oscillator Frequency Range	(Note 15)	●	10	1000 <del>4000</del>	kHz	
$t_{HEO}$	External Oscillator High Period		●	0.125	100	$\mu\text{s}$	
$t_{LEO}$	External Oscillator Low Period		●	0.125	100	$\mu\text{s}$	
$t_{CONV\_1}$	Conversion Time for 1x Speed Mode	50Hz Mode	●	157.2	160.3	163.5	ms
		50Hz Mode (H-Grade)	●	157.2	160.3	165.1	ms
		60Hz Mode	●	131.0	133.6	136.3	ms
		60Hz Mode (H-Grade)	●	131.0	133.6	137.6	ms
		Simultaneous 50Hz/60Hz Mode	●	144.1	146.9	149.9	ms
		Simultaneous 50Hz/60Hz Mode (H-Grade)	●	144.1	146.9	151.0	ms
		External Oscillator	●	41036/ $f_{EOSC}$ (in kHz)		ms	
$t_{CONV\_2}$	Conversion Time for 2x Speed Mode	50Hz Mode	●	78.7	80.3	81.9	ms
		50Hz Mode (H-Grade)	●			82.7	ms
		60Hz Mode	●	65.6	66.9	68.2	ms
		60Hz Mode (H-Grade)	●			68.9	ms
		Simultaneous 50Hz/60Hz Mode	●	72.2	73.6	75.1	ms
		Simultaneous 50Hz/60Hz Mode (H-Grade)	●			75.6	ms
		External Oscillator	●	20556/ $f_{EOSC}$ (in kHz)		ms	
$f_{ISCK}$	Internal SCK Frequency	Internal Oscillator (Note 10)		38.4		kHz	
		External Oscillator (Notes 10, 11)		$f_{EOSC}/8$		kHz	
$D_{ISCK}$	Internal SCK Duty Cycle	(Note 10)	●	45	55	%	
$f_{ESCK}$	External SCK Frequency Range	(Note 10)	●		4000	kHz	

## APPLICATIONS INFORMATION

internal oscillator and 50Hz mode, the extra gain error is 0.061ppm. If an external clock is used, the corresponding extra gain error is  $0.24 \cdot 10^{-6} \cdot f_{EOSC}$ ppm.

The magnitude of the dynamic reference current depends upon the size of the very stable internal sampling capacitors and upon the accuracy of the converter sampling clock. The accuracy of the internal clock over the entire temperature and power supply range is typically better than 0.5%. Such a specification can also be easily achieved by an external clock. When relatively stable resistors (50ppm/°C) are used for the external source impedance seen by  $V_{REF}^+$  and GND, the expected drift of the dynamic current gain error will be insignificant (about 1% of its value over the entire temperature and voltage range). Even for the most stringent applications a one-time calibration operation may be sufficient.

In addition to the reference sampling charge, the reference pins ESD protection diodes have a temperature dependent leakage current. This leakage current, nominally 1nA ( $\pm 10$ nA max), results in a small gain error. A 100 $\Omega$  source resistance will create a 0.05 $\mu$ V typical and 0.5 $\mu$ V maximum full-scale error.

### Output Data Rate

When using its internal oscillator, the LTC2480 produces up to 7.5 samples per second (sps) with a notch frequency of 60Hz, 6.25sps with a notch frequency of 50Hz and 6.82sps with the 50Hz/60Hz rejection mode. The actual output data rate will depend upon the length of the sleep and data output phases which are controlled by the user and which can be made insignificantly short. When operated with an external conversion clock ( $f_0$  connected to an external oscillator), the LTC2480 output data rate can be increased as desired. The duration of the conversion phase is  $41036/f_{EOSC}$ . If  $f_{EOSC} = 307.2$ kHz, the converter behaves as if the internal oscillator is used and the notch is set at 60Hz.

An increase in  $f_{EOSC}$  over the nominal 307.2kHz will translate into a proportional increase in the maximum output data rate. The increase in output rate is nevertheless accompanied by three potential effects, which must be carefully considered.

First, a change in  $f_{EOSC}$  will result in a proportional change in the internal notch position and in a reduction of the converter differential mode rejection at the power line fre-

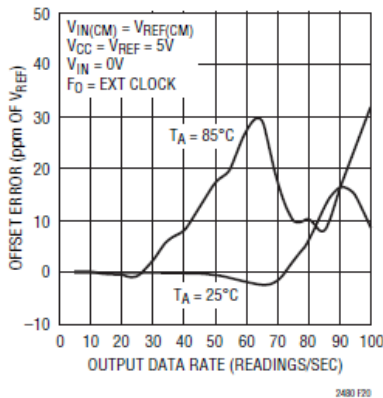


Figure 20. Offset Error vs Output Data Rate and Temperature

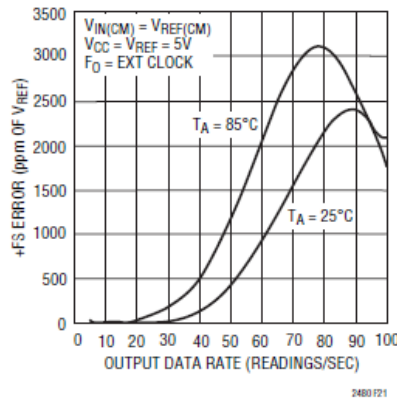


Figure 21. +FS Error vs Output Data Rate and Temperature

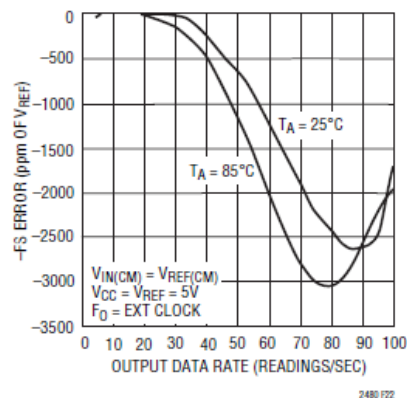


Figure 22. -FS Error vs Output Data Rate and Temperature

## APPLICATIONS INFORMATION

quency. In many applications, the subsequent performance degradation can be substantially reduced by relying upon the LTC2480's exceptional common mode rejection and by carefully eliminating common mode to differential mode conversion sources in the input circuit. The user should avoid single-ended input filters and should maintain a very high degree of matching and symmetry in the circuits driving the  $IN^+$  and  $IN^-$  pins.

Second, the increase in clock frequency will increase proportionally the amount of sampling charge transferred through the input and the reference pins. If large external input and/or reference capacitors ( $C_{IN}$ ,  $C_{REF}$ ) are used, the previous section provides formulae for evaluating the effect of the source resistance upon the converter performance for

any value of  $f_{EOSC}$ . If small external input and/or reference capacitors ( $C_{IN}$ ,  $C_{REF}$ ) are used, the effect of the external source resistance upon the LTC2480 typical performance can be inferred from Figures 13, 14, 15 and 16 in which the horizontal axis is scaled by  $307200/f_{EOSC}$ .

Third, an increase in the frequency of the external oscillator above 1MHz (a more than  $3\times$  increase in the output data rate) will start to decrease the effectiveness of the internal autocalibration circuits. This will result in a progressive degradation in the converter accuracy and linearity. Typical measured performance curves for output data rates up to 100 readings per second are shown in Figures 20 to 27. In order to obtain the highest possible level of accuracy from this converter at output data rates above 20 readings per

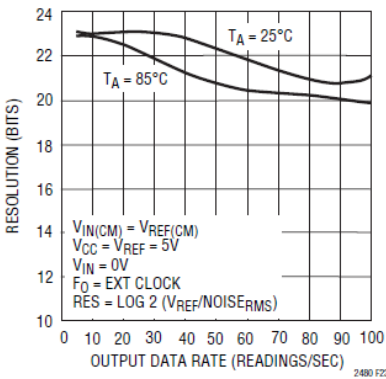


Figure 23. Resolution ( $NOISE_{RMS} \leq 1LSB$ ) vs Output Data Rate and Temperature

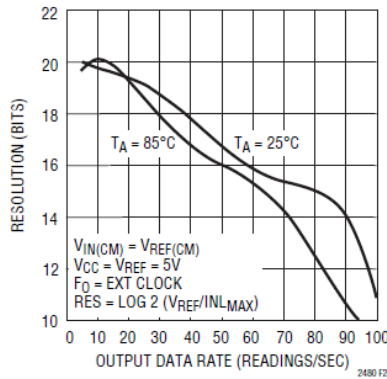


Figure 24. Resolution ( $INL_{MAX} \leq 1LSB$ ) vs Output Data Rate and Temperature

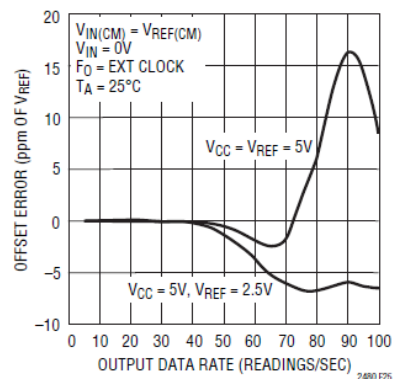


Figure 25. Offset Error vs Output Data Rate and Reference Voltage

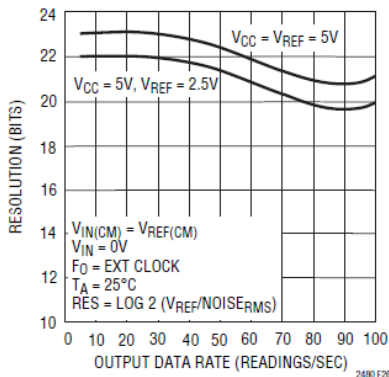


Figure 26. Resolution ( $NOISE_{RMS} \leq 1LSB$ ) vs Output Data Rate and Reference Voltage

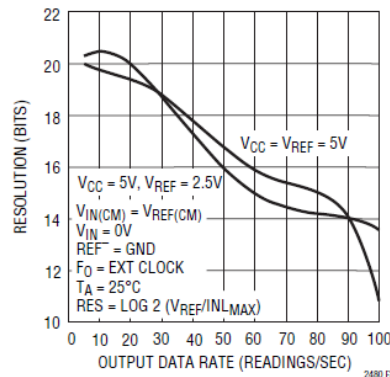


Figure 27. Resolution ( $INL_{MAX} \leq 1LSB$ ) vs Output Data Rate and Reference Voltage